

Paper Id: **120250**Roll No. 

--	--	--	--	--	--	--	--	--	--

**B. TECH.****(SEM VIII) THEORY EXAMINATION 2018-19****ELECTRICAL & ELECTRONICS ENGINEERING MATERIALS****Time: 3 Hours****Total Marks: 100****Note: 1.** Attempt all Sections. If require any missing data; then choose suitably.**SECTION A****1. Attempt all questions in brief. 2 x 10 = 20**

- a. Draw (112) & (111) planes in simple cubic cell.
- b. Write ohms law for electron theory.
- c. What do you mean by doping in semiconductor?
- d. What is Curie temperature?
- e. Explain Seebeck, Thomson Effect in thermocouple.
- f. Mobility of electrons & holes in intrinsic semiconductor of germanium at room temperature are  $3600 \text{ cm}^2/\text{v-s}$  &  $1700 \text{ cm}^2/\text{v-s}$ . if electrons & holes are equal to  $3.2 \times 10^{12} / \text{cm}^3$ , find out conductivity.
- g. What is Magnetostriction and its types?
- h. Explain Body centered cubic structure (BCC)
- i. Write composition of Alnico.
- j. Explain Metallic bonding with diagram.

**SECTION B****2. Attempt any three of the following: 10x3=30**

- a. Explain the effect of temperature on electrical conductivity of metals. The following data refer to copper-  
Density= $8.94 \text{ gm/cm}^3$ , resistivity= $1.73 \times 10^{-8} \Omega\text{m}$ ; atomic weight = 63.5  
Calculate the mobility and average time of collision of electron in the copper.
- b. Explain Bragg's, Law. X ray of wavelength  $1.54 \text{ \AA}$  are used for calculating  $d_{200}$  in Ni. The reflection angle is  $9.5^\circ$ , what is size of unit cell.
- c. Using drift and diffusion current in a semiconductor, find an expression of continuity equation.
- d. Draw Diagrams giving energy band structure of an Conductor, insulator & semiconductor. Explain difference in their conductivity?
- e. Describe soft and hard magnetic material indicates their composition, property also draw their B-H curve.

**SECTION C****3. Attempt any one part of the following:**

- a. State Ionic, Covalent & Metallic bonds with their characteristics.
- b. Explain Miller indices, write procedure to find it. Also prove that  $d_{100}:d_{110}:d_{111}:\sqrt{6}:\sqrt{3}:\sqrt{2}$  for a simple cubic system.



**4. Attempt any one part of the following:**

- a. Write short note- Soft Magnetic material, Hard Magnetic material also draw their B-H curve.
- b. Explain Ferromagnetism, Ferri magnetism, Anti ferromagnetism material with their properties.

**5. Attempt any one part of the following:**

- a. With the help of neat sketches and characteristic curves explain the operation of the Junction FET.
- b. Calculate the drift velocity of electrons & holes in (i) Si (ii) Ge at 300K when applied electric field is 50v/cm take  $\mu_p = 500 \text{ cm}^2/\text{v-s}$ ,  $\mu_n = 1500 \text{ cm}^2/\text{v-s}$  for Si,  $\mu_p = 3700 \text{ cm}^2/\text{v-s}$ ,  $\mu_n = 3600 \text{ cm}^2/\text{v-s}$  for Ge.

**6. Attempt any one part of the following:**

- a. Write short notes on followings:
  - (i) Fermi surface
  - (ii) Energy gap
  - (iii) Energy level
- b. Find energy loss per hour in Iron subjected to magnetization 50 c/s . the iron weight 50 kg & hysteresis loop area 250 joules /  $\text{m}^3$ . Density of iron= 7000  $\text{kg}/\text{m}^3$

**7. Attempt any one part of the following:**

- a. What is Hall Effect; derive the relation between hall coefficient and current density. Assume presence of only one charge carrier.
- b. Explain the term superconductivity. Name some of the important superconductivity elements compound and alloys.